

BTA312 series D and E

12 A Three-quadrant triacs high commutation

Rev. 01 — 16 April 2007

Product data sheet

1. Product profile

1.1 General description

Passivated, new generation, high commutation triacs in a SOT78 plastic package

1.2 Features

- Sensitive gate
- Very high commutation performance maximized at each gate sensitivity
- High immunity to dV/dt

1.3 Applications

- High power motor control - e.g. washing machines, vacuum cleaners
- Electronic thermostats
- Refrigeration and air conditioning compressors

1.4 Quick reference data

- $V_{\text{DRM}} \leq 600 \text{ V}$ (BTA312-600D)
- $V_{\text{DRM}} \leq 600 \text{ V}$ (BTA312-600E)
- $V_{\text{DRM}} \leq 800 \text{ V}$ (BTA312-800E)
- $I_{\text{TSM}} \leq 95 \text{ A}$ ($t = 20 \text{ ms}$)
- $I_{\text{GT}} \leq 5 \text{ mA}$ (BTA312-600D)
- $I_{\text{GT}} \leq 10 \text{ mA}$ (BTA312-600E)
- $I_{\text{GT}} \leq 10 \text{ mA}$ (BTA312-800E)
- $I_{\text{T(RMS)}} \leq 12 \text{ A}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)	SOT78 (TO-220AB)	sym051
2	main terminal 2 (T2)		
3	gate (G)		
mb	mounting base; main terminal 2 (T2)		

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BTA312-600D	SC-46	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78
BTA312-600E			
BTA312-800E			

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA312-600D; BTA312-600E	[1]	600	V
		BTA312-800E	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 101\text{ }^{\circ}\text{C}$; see Figure 4 and 5	-	12	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25\text{ }^{\circ}\text{C}$ prior to surge; see Figure 2 and 3			
		$t = 20\text{ ms}$	-	95	A
		$t = 16.7\text{ ms}$	-	105	A
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	45	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{TM}} = 20\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	+150	$^{\circ}\text{C}$
T_{j}	junction temperature		-	125	$^{\circ}\text{C}$

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

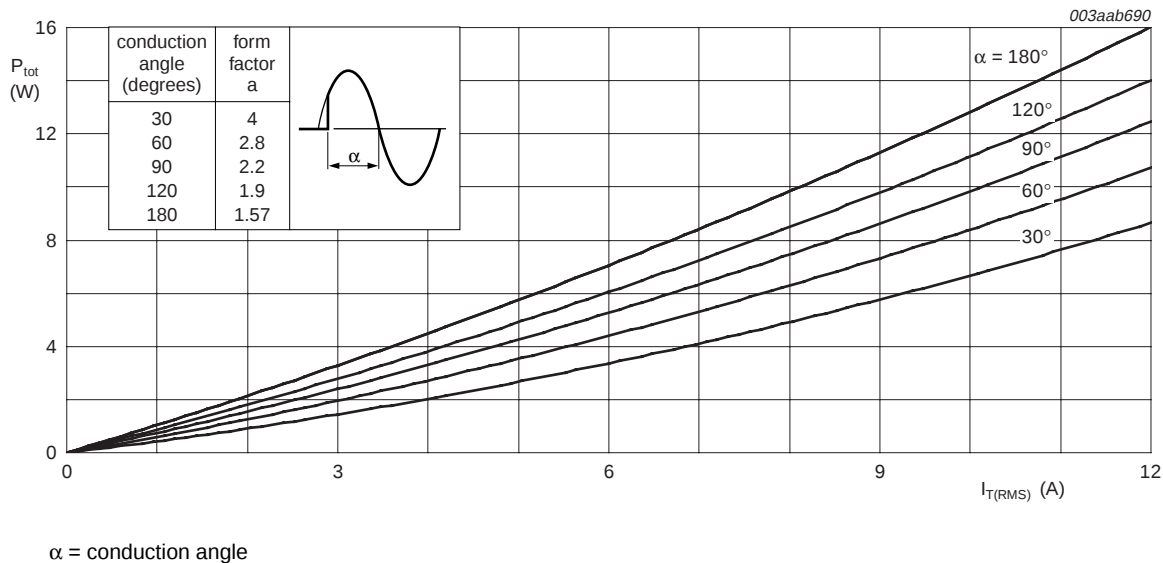


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

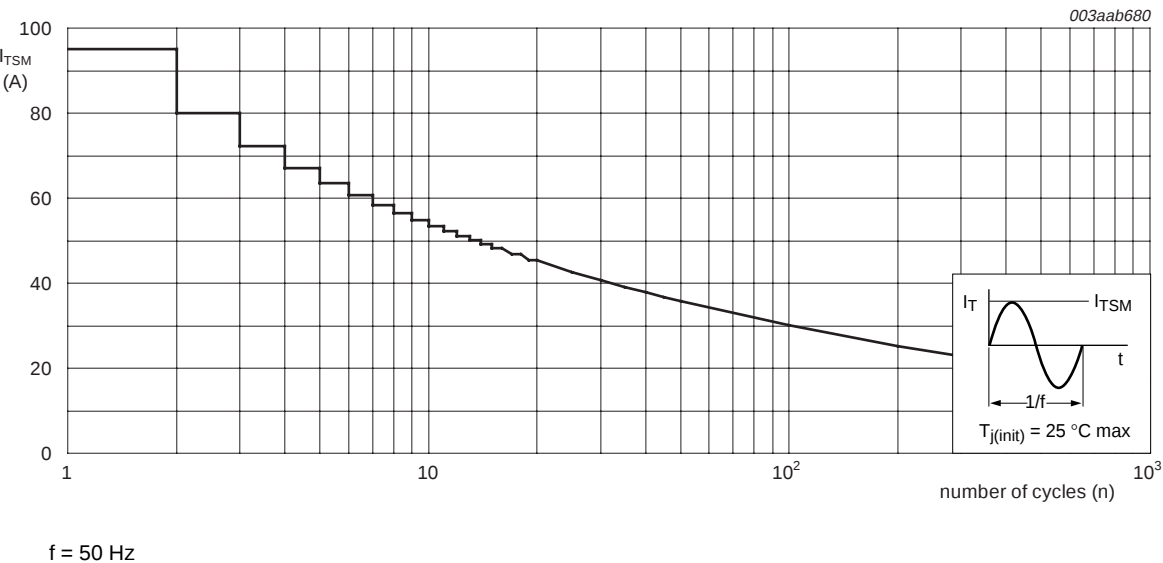
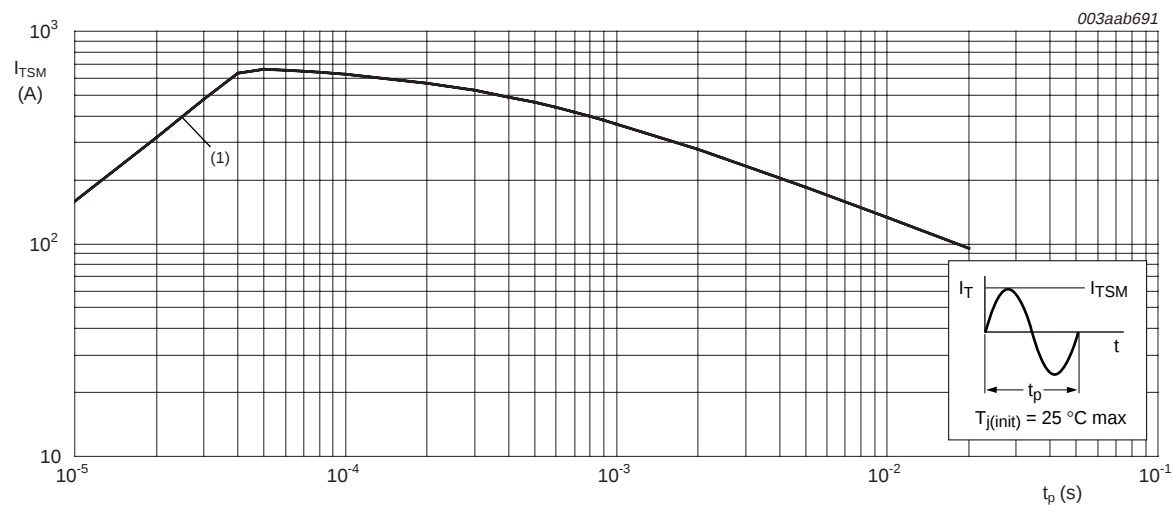
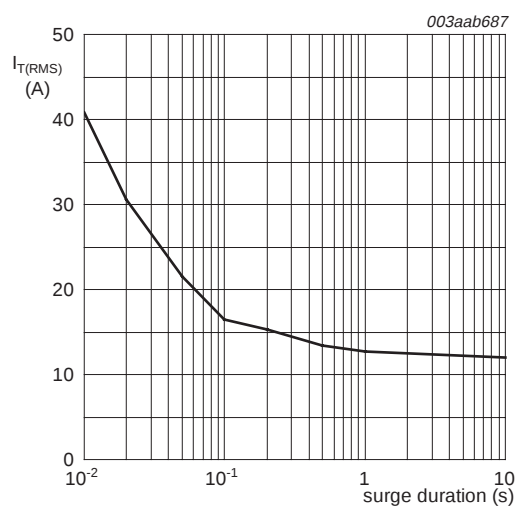


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20\text{ ms}$
(1) di_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values



$f = 50\text{ Hz}$
 $T_{mb} = 101^\circ\text{C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

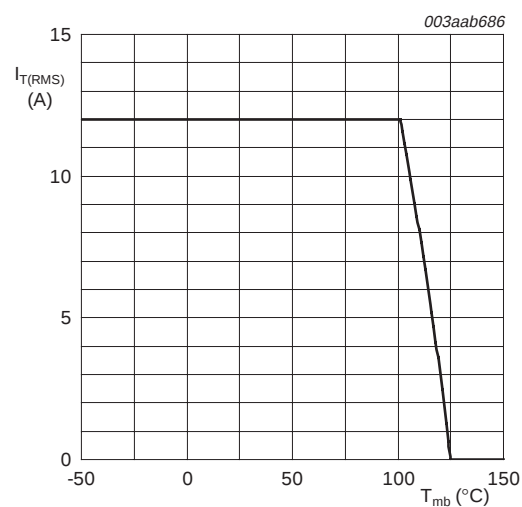
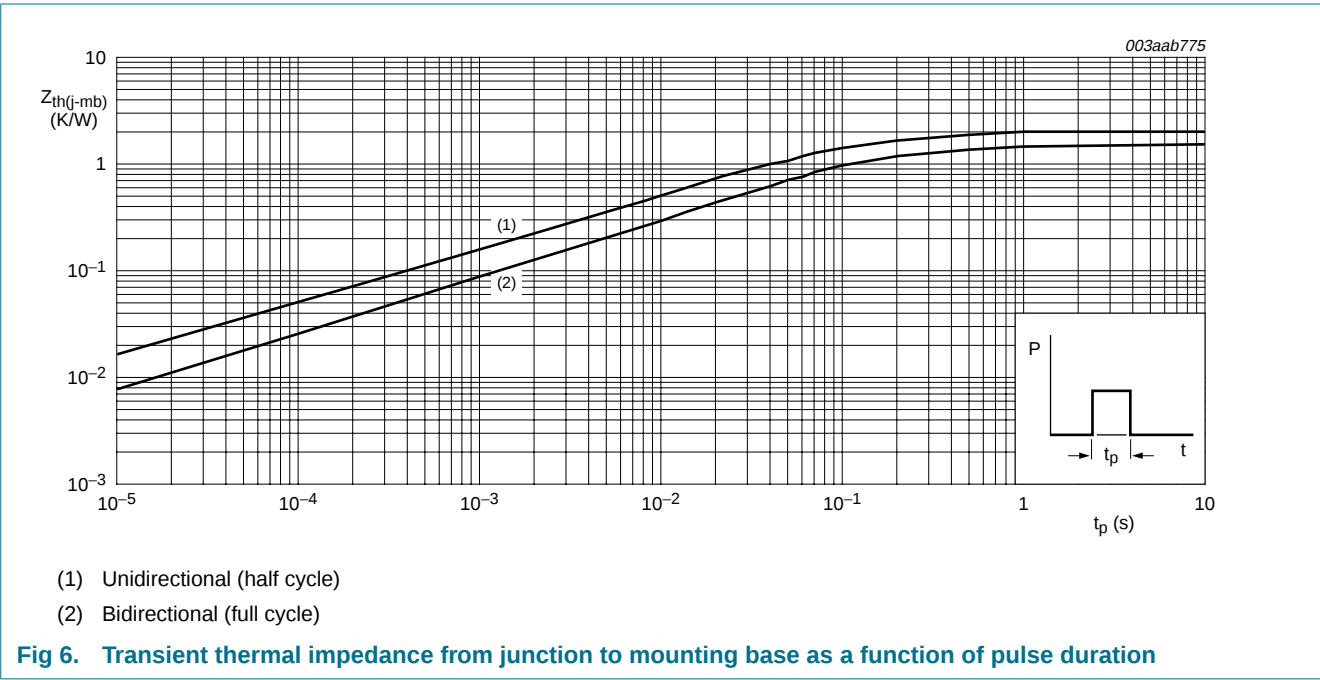


Fig 5. RMS on-state current as a function of mounting base temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; see Figure 6	-	-	2.0	K/W
		full cycle; see Figure 6	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Static characteristics

Table 5. Static characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	BTA312-600D			BTA312-600E BTA312-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 8							
		T2+ G+	-	-	5	-	-	10	mA
		T2+ G-	-	-	5	-	-	10	mA
		T2- G-	-	-	5	-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; see Figure 10							
		T2+ G+	-	-	10	-	-	25	mA
		T2+ G-	-	-	15	-	-	30	mA
		T2- G-	-	-	15	-	-	25	mA
I_H	holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; see Figure 11	-	-	10	-	-	15	mA
V_T	on-state voltage	$I_T = 15\text{ A}$; see Figure 9	-	1.3	1.6	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 7	-	0.7	1.5	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.25	0.4	-	0.25	0.4	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$	-	0.1	0.5	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	BTA312-600D			BTA312-600E BTA312-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_J = 125\text{ }^{\circ}\text{C}$; exponential waveform; gate open circuit	20	-	-	50	-	-	V/ μs
di_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_J = 125\text{ }^{\circ}\text{C}$; $I_{T(RMS)} = 12\text{ A}$; without snubber; gate open circuit	1	-	-	3	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_J = 125\text{ }^{\circ}\text{C}$; $I_{T(RMS)} = 12\text{ A}$; $dV/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	1.5	-	-	6	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_J = 125\text{ }^{\circ}\text{C}$; $I_{T(RMS)} = 12\text{ A}$; $dV/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	4.5	-	-	10	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	-	2	-	μs

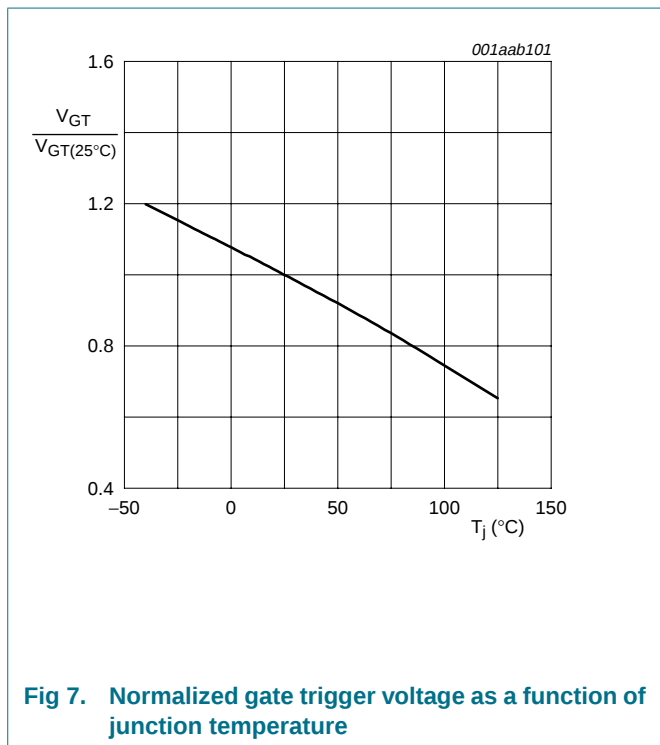


Fig 7. Normalized gate trigger voltage as a function of junction temperature

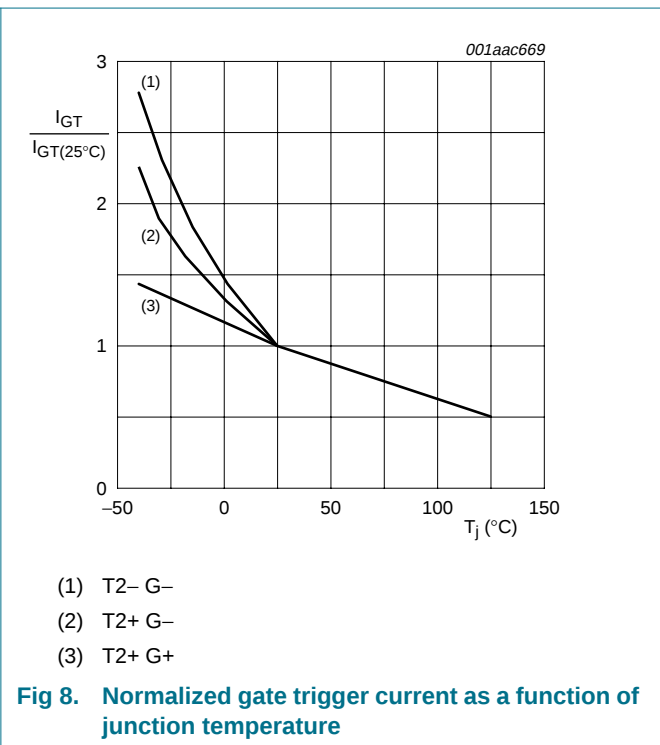
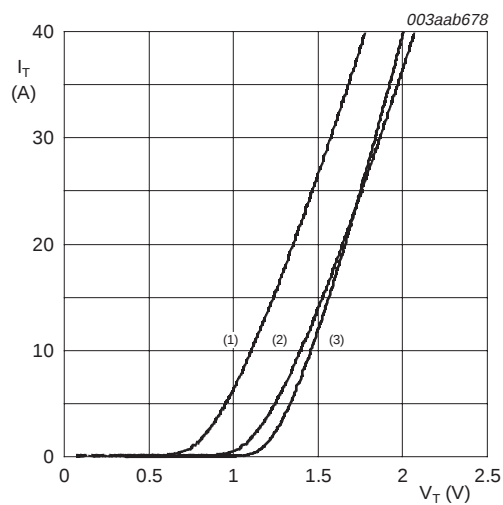


Fig 8. Normalized gate trigger current as a function of junction temperature



$V_0 = 1.127 \text{ V}$

$R_s = 0.027 \text{ } \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

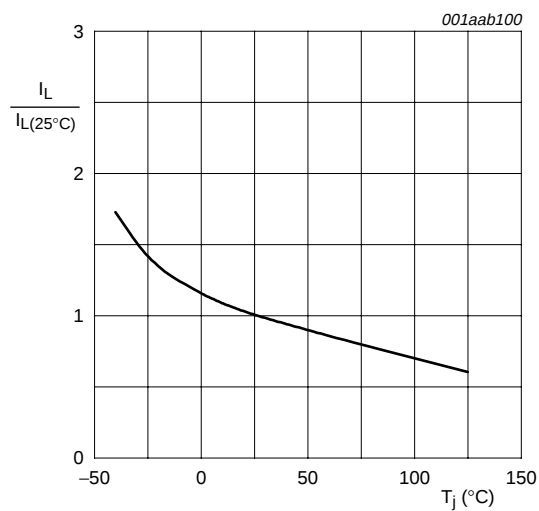


Fig 10. Normalized latching current as a function of junction temperature

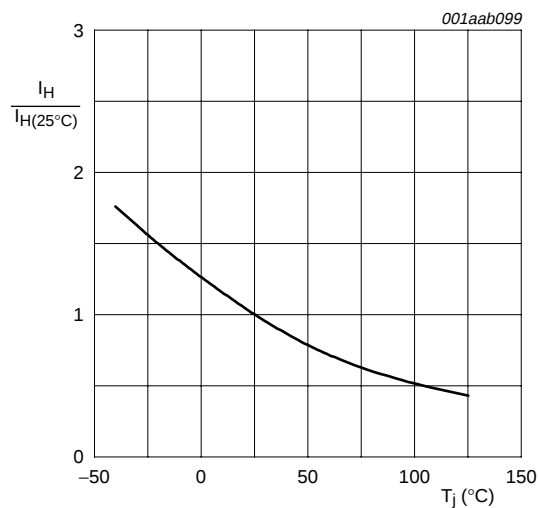


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

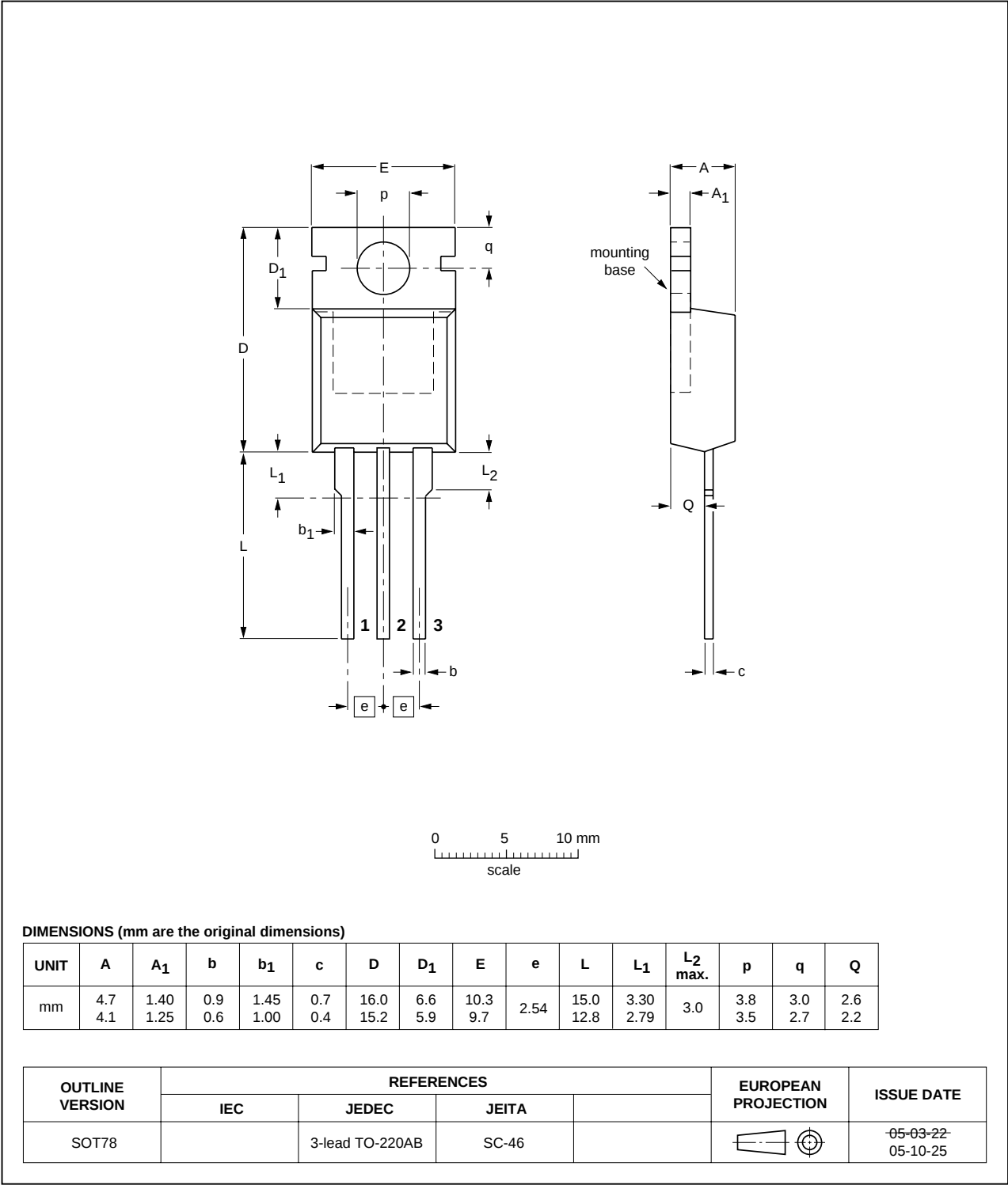


Fig 12. Package outline SOT78 (3-lead TO-220AB)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA312_SER_D_E_1	20070416	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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